

Silicon Hot – Carrier Diodes

These devices are designed primarily for high–efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low–cost,high–volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

- Extremely Low Minority Carrier Lifetime 15 ps (Typ)
- Very Low Capacitance 1.0 pF @ V _R = 20 V
- High Reverse Voltage to 70 Volts
- Low Reverse Leakage 200 nA (Max)



70 VOLTS HIGH-VOLTAGE SILICON HOT-CARRIER DETECTOR AND SWITCHING DIODES



CASE 318-08, STYLE8 SOT- 23 (TO-236AB)

MAXIMUM RATINGS (T_J = 125°C unless otherwise noted)

		MBD701	MMBD701LT1	
Rating	Symbol	Va	Unit	
Reverse Voltage	V _R		Volts	
Forward Power Dissipation	PF			
@ T _A = 25°C		280	200	mW
Derate above 25°C		2.8	2.0	mW/°C
Operating Junction	ΤJ			°C
Temperature Range		–55 t		
Storage Temperature Range	T stg	-55	°C	

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CATHODE

DEVICE MARKING

MMBD701LT1 = 5H

ELECTRICAL CHARACTERISTICS (T A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	typ	Max	Unit
Reverse Breakdown Voltage (I $_{R}$ = 10µAdc)	V (BR)R	70	_	_	Volts
Total Capacitance (V $_{R}$ = 20 V, f = 1.0 MHz) Figure 1	Ст	_	0.5	1.0	pF
Reverse Leakage (V $_{R}$ = 35 V) Figure 3	I _R	—	9.0	200	nAdc
Forward Voltage (I _F = 1.0 mAdc) Figure 4	V _F	_	0.42	0.5	Vdc
Forward Voltage (I _F = 10 mAdc) Figure 4	V F	_	0.7	1.0	Vdc

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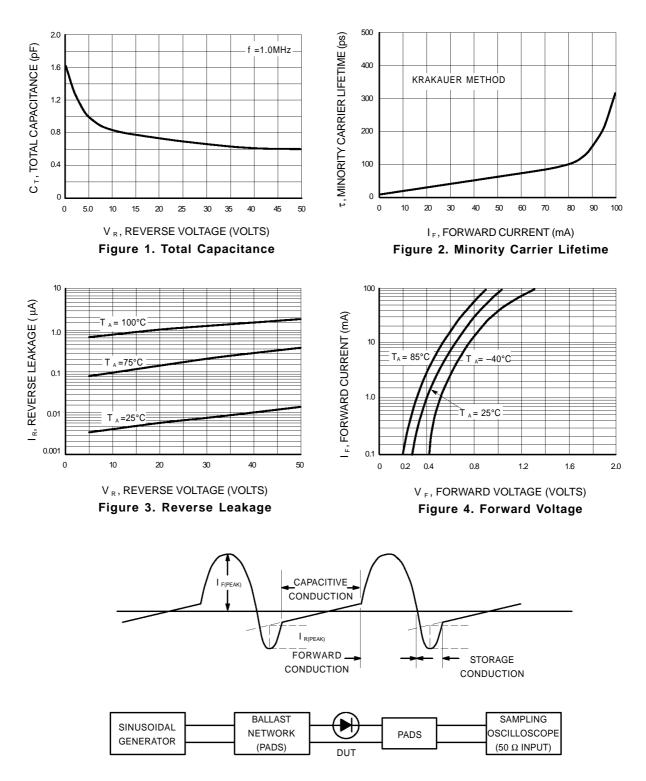
ANODE

NOTE: MMBD701LT1 is also available in bulk packaging. Use MMBD701L as the device title to order this device in bulk.



查询"MMBD7011.T1G"供应商

MBD701 MMBD701LT1



TYPICAL ELECTRICAL CHARACTERISTICS

Figure 5. Krakauer Method of Measuring Lifetime